



40V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max (A) T _A = +25°C	
-40V	$25m\Omega$ @ V _{GS} = -10V	-7.2A	
-40V	45mΩ @ V _{GS} = -4.5V	-5.3A	

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Motor controls
- Backlighting
- DC-DC converters
- Printer equipment

Features and Benefits

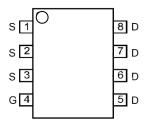
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low R_{DS(ON)} Minimizes Conduction Losses
- Fast Switching Speed Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Qsuffix) part. A listing can be found at https://www.diodes.com/products/automotive-products/.
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
- https://www.diodes.com/quality/product-definitions/

Mechanical Data

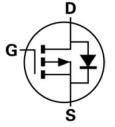
- Package: SO-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (Approximate)







Pin-Out Top View



Internal Schematic

Ordering Information (Note 4)

Part Number	Packago	Packing		
Fait Number	Раскауе	Qty.	Carrier	
DMP4026LSS-13	SO-8	2,500	Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



O':| = Manufacturer's Marking
P4026LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 23 = 2023)
WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	VDSS	-40	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	lD	-7.2 -5.7	А
Maximum Body Diode Forward Current (Note 6)	ls	-7.2	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-46	Α
Pulsed Body Diode Forward Current (10µs Pulse, Do	lsм	-46	Α
Avalanche Current, L = 0.3mH	las	-20	Α
Avalanche Energy, L = 0.3mH	Eas	62	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	82.7	°C/W
Total Power Dissipation (Note 6)		Pp	2.0	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		Reja	60.3	°C/W
Thermal Resistance, Junction to Case	Rejc	8.2	C/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

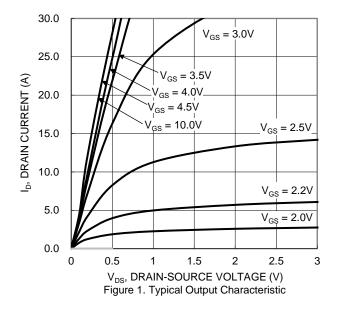
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-40	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	-1.0	μA	V _{DS} = -40V, V _{GS} = 0V
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(TH)	-0.8	_	-1.8	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
Static Drain-Source On-Resistance	D	_	13.9	25	mΩ	$V_{GS} = -10V, I_D = -3A$
Static Dialif-Source Off-Resistance	R _{DS(ON)}	_	17.2	45	11122	$V_{GS} = -4.5V, I_{D} = -3A$
Diode Forward Voltage	VsD	_	-0.7	-1.0	V	$V_{GS} = 0V$, $I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	2083			V _{DS} = -20V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	Coss	_	221		pF	
Reverse Transfer Capacitance	Crss	_	191			
Gate Resistance	Rg	_	2.5	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
Total Gate Charge (V _{GS} = -10V)	Q_{G}	_	45	_		
Total Gate Charge (V _{GS} = -4.5V)	QG	_	23.5	_	nC	Vps = -20V. Ip = -3A
Gate-Source Charge	Qgs	_	5	_	nc nc	VDS = -20V, ID = -3A
Gate-Drain Charge	Q _{GD}	_	6.7	_		
Turn-On Delay Time	t _D (ON)	_	4.3	_		$V_{GS} = -10V$, $V_{DD} = -20V$, $R_{G} = 6\Omega$,
Turn-On Rise Time	t _R	_	4.8	_		
Turn-Off Delay Time	tD(OFF)	_	71	_	ns	I _D = -3A
Turn-Off Fall Time	t _F	_	24	_		
Body Diode Reverse Recovery Time	trr	_	17.3	_	ns	Is = -3A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Qrr	_	8.7	_	nC	Is = -3A, di/dt = 100A/µs

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect. Notes:

^{8.} Guaranteed by design. Not subject to product testing.





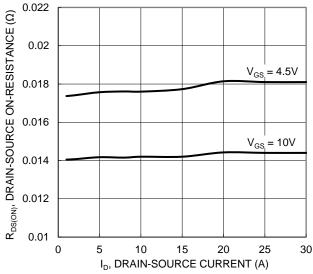


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

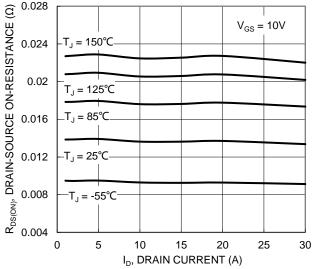
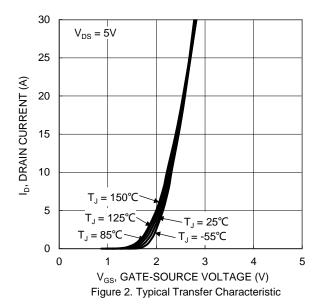
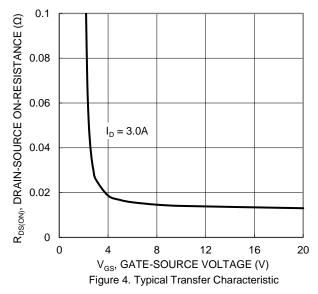


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





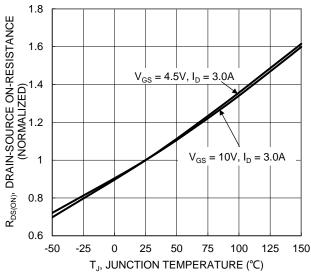


Figure 6. On-Resistance Variation with Junction Temperature



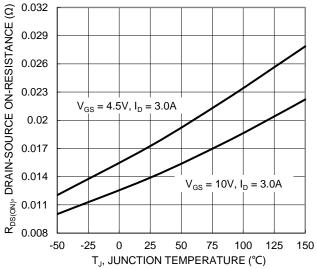
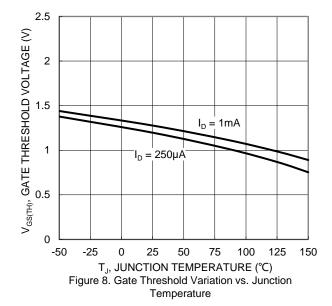
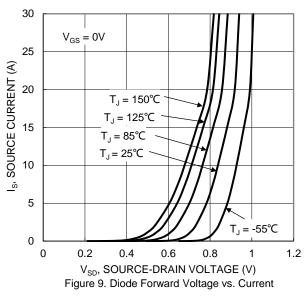
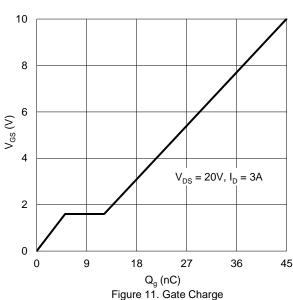
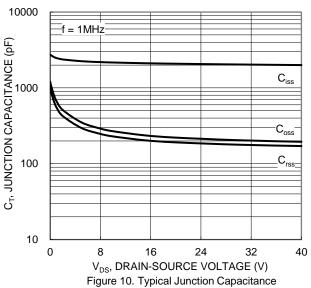


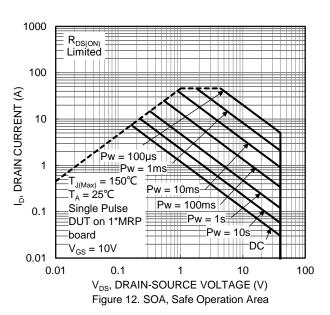
Figure 7. On-Resistance Variation with Junction Temperature













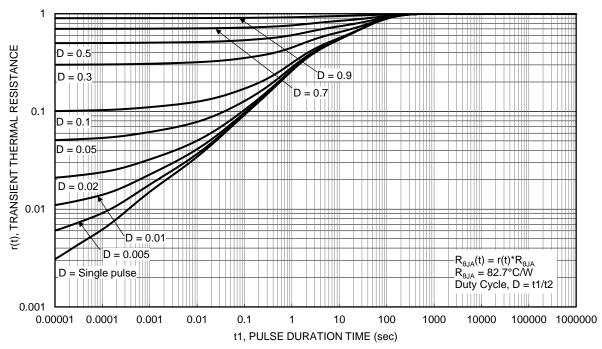


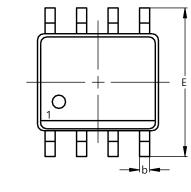
Figure 13. Transient Thermal Resistance

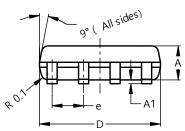


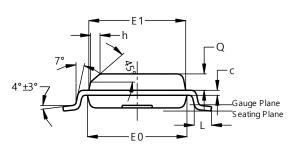
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.







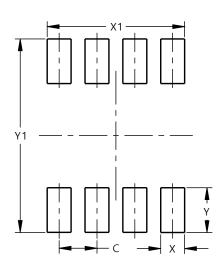


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
E	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h			0.35		
L	0.62	0.82	0.72		
Ø	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)				
С	1.27				
Х	0.802				
X1	4.612				
Y	1.505				
Y1	6.50				

March 2023



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